



FORM PTO-1449 (Modified)

LIST OF PATENTS AND PUBLICATIONS
FOR APPLICANT'S INFORMATION
DISCLOSURE STATEMENT

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APPLICANT:
J. O. Chu et al.FILING DATE:
April 20, 2001

GROUP: 2811

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

EXAMINER INITIALS		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPRO.)
<i>CM</i>	AA	5,906,680	5/25/1999	Meyerson	117	88	
	AB						
	AC						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
	AD							
	AE							
	AF							

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

<i>CM</i>	AG	E. Kasper et al., "Growth of 100 GHz SiGe-Heterobipolar Transistor (HBT) Structures," Jpn J Appl Phys, Vol. 33 Pt. 1, No. 4B, April 1994, pp. 2415-2418.
<i>CM</i>	AH	H.J. Osten et al., in the paper entitled "Carbon Doped SiGe Heterojunction Bipolar Transistors for High Frequency Applications," IEEE BCTM 7.1, 1999, pp. 109-116.
	AI	
	AJ	

EXAMINER

J. O. Chu et al.

DATE CONSIDERED

4/1/02

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.